Technical Data
DIODE

DISCRETE SEMICONDUCTOR INDUSTRIES

maximum ratings

Voltage, Reverse (VZ)	12.0	V	NO.	1N3022B-M
Voltage, Reverse Peak (VRM)		V	TYPE	1W-ZENER
Current at VR = OV (IO)		A		
Current Average Rectified (IF)		A		
Current Surge Peak (IZM)	0.08	A	CASE	DO-13
Current, Surge (IFM) at tp =		A		MIL-S-19500
Max. Power Dissipation (PT) at TC = 25 °C	1.0	W		BURN-IN 48h/125°C
Max. Thermal Resistance (Rth J-A)	150.0	°C/W		
Max. Junction Temperature (TJ)	175.0	°C		

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	VZ	IZ = 21.0 mA, tp = 100.0 µs, dc = 0.1 %	11.4	12.6	V
2.	RZ	IZ = 21.0 mA, ΔIZ = 10.0 % IZ, f = 1.0 kHz	-	9.0	Ω
3.	RZ	IZ = 0.25 mA	-	700.0	Ω
4.	IR	VR = 9.1 V	-	2.0	µA
5.	VF	IF = 200.0 mA (1)	-	1.5	V
6.					
7.					
8.					
9.					
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11.					
12.					
13.					
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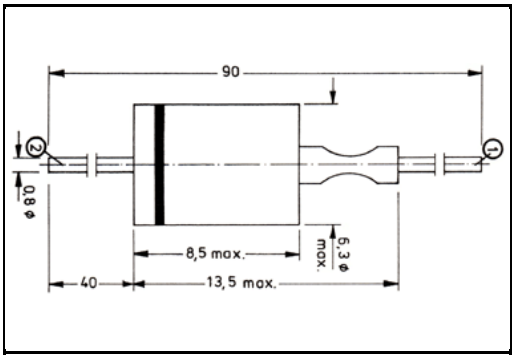
16.					
17.					
18.					
19.					
20.					

Notes (1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %

DIMENSIONS in mm



Marking 1N3022B-M + GREEN DOT

Customer GENERAL PURPOSE